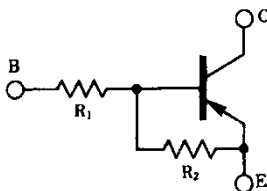


COMPOUND TRANSISTOR BN1A3Q

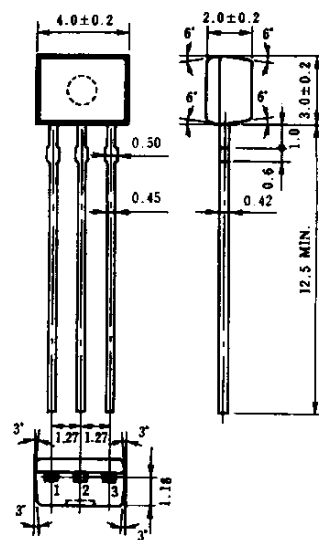
on-chip resistor PNP silicon epitaxial transistor
For mid-speed switching

FEATURES

- On-chip bias resistor
($R_1 = 1.0 \text{ k}\Omega$, $R_2 = 10 \text{ k}\Omega$)
- Complementary transistor with BA1A3Q



PACKAGE DRAWING (UNIT: mm)



Electrode Connection

1. Emitter
2. Collector
3. Base

ABSOLUTE MAXIMUM RATINGS ($T_a = 25^\circ\text{C}$)

Parameter	Symbol	Ratings	Unit
Collector to base voltage	V_{CBO}	-60	V
Collector to emitter voltage	V_{CEO}	-50	V
Emitter to base voltage	V_{EBO}	-5	V
Collector current (DC)	$I_{C(DC)}$	-100	mA
Collector current (Pulse)	$I_{C(pulse)}$ *	-200	mA
Total power dissipation	P_T	250	mW
Junction temperature	T_j	150	$^\circ\text{C}$
Storage temperature	T_{stg}	-55 to +150	$^\circ\text{C}$

* $PW \leq 10 \text{ ms}$, duty cycle $\leq 50 \%$

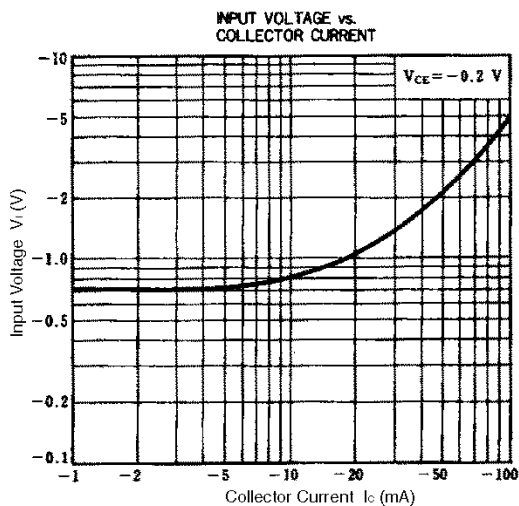
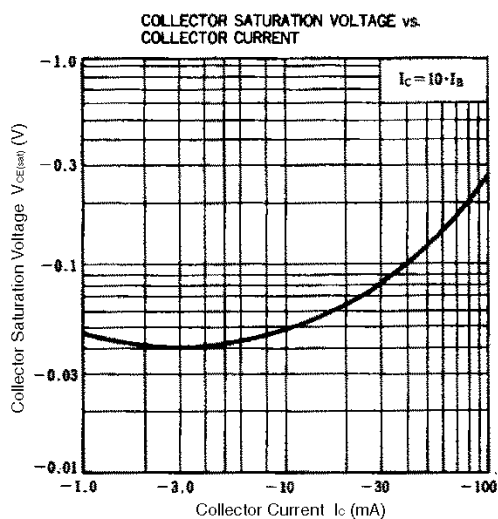
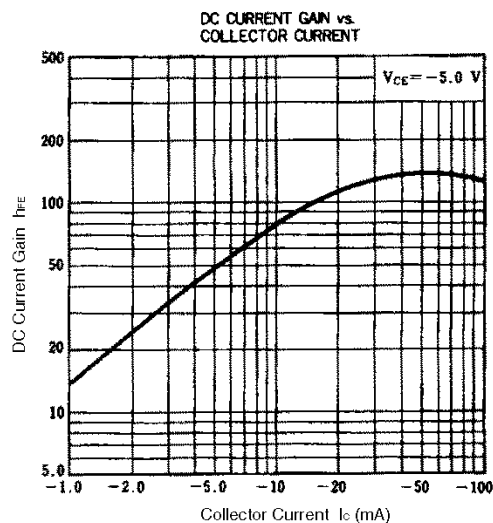
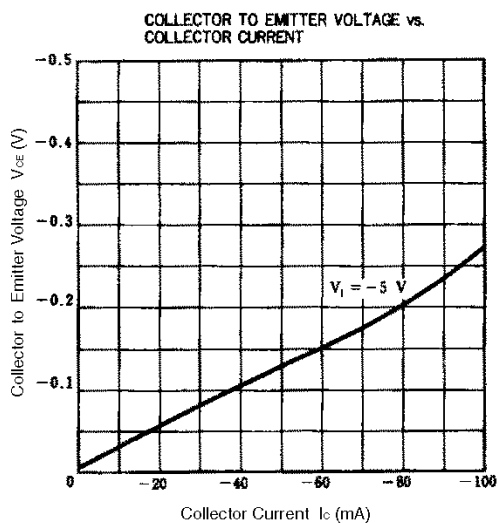
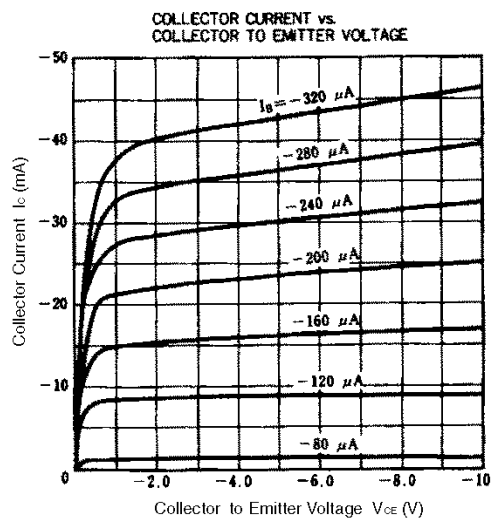
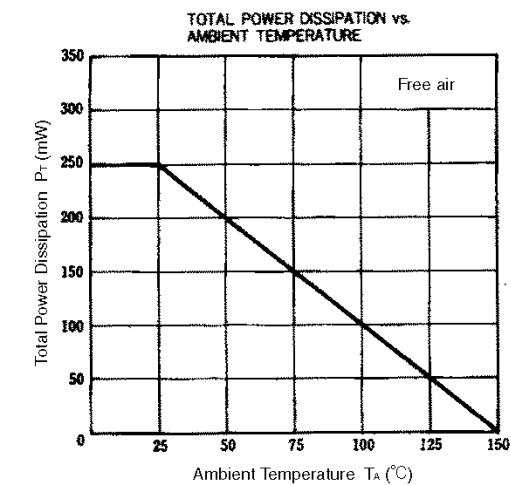
ELECTRICAL CHARACTERISTICS ($T_a = 25^\circ\text{C}$)

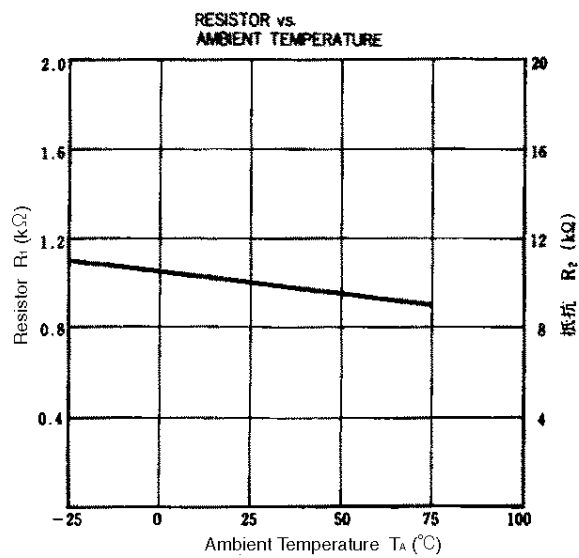
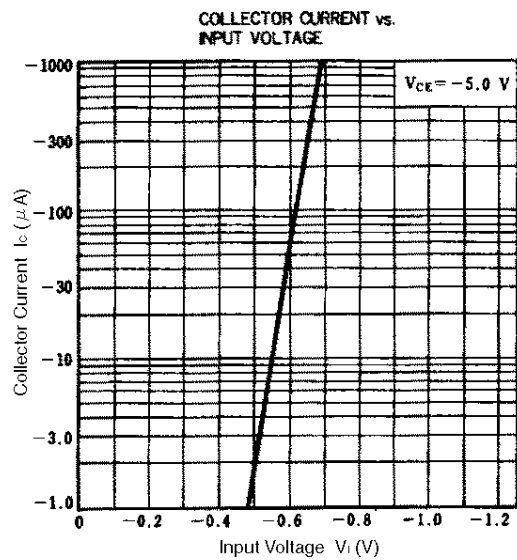
Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Collector cutoff current	I_{CBO}	$V_{CB} = -50 \text{ V}$, $I_E = 0$			-100	nA
DC current gain	h_{FE1} **	$V_{CE} = -5.0 \text{ V}$, $I_C = -5.0 \text{ mA}$	35	60	80	-
DC current gain	h_{FE2} **	$V_{CE} = -5.0 \text{ V}$, $I_C = -50 \text{ mA}$	80	200		-
Collector saturation voltage	$V_{CE(sat)}$ **	$I_C = -5.0 \text{ mA}$, $I_B = -0.25 \text{ mA}$		-0.04	-0.2	V
Low level input voltage	V_{IL} **	$V_{CE} = -5.0 \text{ V}$, $I_B = -100 \mu\text{A}$		-0.7	-0.5	V
High level input voltage	V_{IH} **	$V_{CE} = -0.2 \text{ V}$, $I_C = -5.0 \text{ mA}$	-2.0	-1.0		V
Input resistance	R_1		0.7	1.0	1.3	$\text{k}\Omega$
E-to-B resistance	R_2		7	10	13	$\text{k}\Omega$
Turn-on time	t_{on}	$V_{CC} = -5 \text{ V}$, $R_L = 1 \text{ k}\Omega$			0.2	μs
Storage time	t_{stg}	$V_i = -5 \text{ V}$, $PW = 2 \mu\text{s}$			5.0	μs
Turn-off time	t_{off}	duty cycle $\leq 2 \%$			6.0	μs

** $PW \leq 350 \mu\text{s}$, duty cycle $\leq 2 \%$

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TYPICAL CHARACTERISTICS ($T_a = 25^\circ\text{C}$)





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